

L Number	Hits	Search Text	DB	Time stamp
1	14	(NMOS and PMOS and mass and (tensile adj stress) and source and drain and gate and electrode and polysilicon and silicon) and (substrate or internal or stress or tensile or channel or inactive or ions or "70" or mass or silicon or oxide or polysilicon or gate or electrode or strained or transistor or MOS or bird or beak)	USPAT	2004/09/14 16:50
2	1	NMOS and PMOS and mass and (tensile adj stress) and source and drain and gate and electrode and polysilicon and silicon and bird and beak	USPAT	2004/09/14 16:56
3	1	("6682965").PN.	USPAT	2004/09/14 16:56
4	1	((("6682965").PN.) and (substrate or internal or stress or tensile or channel or inactive or ions or "70" or mass or silicon or oxide or polysilicon or gate or electrode or strained or transistor or MOS or bird or beak)	USPAT	2004/09/14 16:59
5	1	("6750486").PN.	USPAT	2004/09/14 16:59
6	1	((("6750486").PN.) and (substrate or internal or stress or tensile or channel or inactive or ions or "70" or mass or silicon or oxide or polysilicon or gate or electrode or strained or transistor or MOS or bird or beak or NMOS or PMOS or transistor or ion or number or Arsenic or boron or phospheric)	USPAT	2004/09/14 17:09
7	1610	257/103	USPAT	2004/09/14 17:07
8	1188	257/192	USPAT	2004/09/14 17:07
9	324	257/213	USPAT	2004/09/14 17:07
10	89	257/265	USPAT	2004/09/14 17:07
11	906	257/288	USPAT	2004/09/14 17:08
12	161	257/63	USPAT	2004/09/14 17:08
13	447	257/334	USPAT	2004/09/14 17:08
14	1029	257/335	USPAT	2004/09/14 17:08
15	2944	257/347	USPAT	2004/09/14 17:08
16	1722	257/401	USPAT	2004/09/14 17:08
17	725	257/565	USPAT	2004/09/14 17:08
18	670	257/414	USPAT	2004/09/14 17:09
19	1	("5815223").PN.	USPAT	2004/09/14 17:09
20	1	((("5815223").PN.) and (substrate or internal or stress or tensile or channel or inactive or ions or "70" or mass or silicon or oxide or polysilicon or gate or electrode or strained or transistor or MOS or bird or beak or NMOS or PMOS or transistor or ion or number or Arsenic or boron or phospheric)	USPAT	2004/09/14 17:09
-	0	NMOS and PMOS and (mass adj number) and (tensile adj stress) and source and drain and gate and electrode and polysilicon and silicon	USPAT	2004/09/14 14:00
-	14	NMOS and PMOS and mass and (tensile adj stress) and source and drain and gate and electrode and polysilicon and silicon	USPAT	2004/09/14 16:51
-	11	NMOS and PMOS and mass and (tensile adj stress) and source and drain and gate and electrode and polysilicon and silicon and number	USPAT	2004/09/14 14:01
-	14	(NMOS and PMOS and mass and (tensile adj stress) and source and drain and gate and electrode and polysilicon and silicon) and (substrate or internal or stress or tensile or channel or inactive or ions or "70" or mass or silicon or oxide or polysilicon or gate or electrode or strained or transistor or MOS)	USPAT	2004/09/14 16:56

9/14/04